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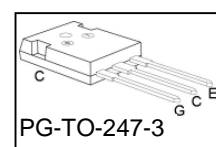
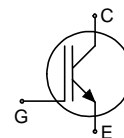


TrenchStop® Series

**IGW40T120**

Low Loss IGBT in TrenchStop® and Fieldstop technology

- Short circuit withstand time – 10μs
- Designed for :
  - Frequency Converters
  - Uninterrupted Power Supply
- TrenchStop® and Fieldstop technology for 1200 V applications offers :
  - very tight parameter distribution
  - high ruggedness, temperature stable behavior
- NPT technology offers easy parallel switching capability due to positive temperature coefficient in  $V_{CE(sat)}$
- Low EMI
- Low Gate Charge
- Qualified according to JEDEC<sup>1</sup> for target applications
- Pb-free lead plating; RoHS compliant
- Complete product spectrum and PSpice Models : <http://www.infineon.com/igbt/>



Type	$V_{CE}$	$I_C$	$V_{CE(sat), T_j=25^\circ C}$	$T_{j,max}$	Marking Code	Package
IGW40T120	1200V	40A	1.7V	150°C	G40T120	PG-TO-247-3

**Maximum Ratings**

Parameter	Symbol	Value	Unit
Collector-emitter voltage	$V_{CE}$	1200	V
DC collector current	$I_C$	75	A
$T_C = 25^\circ C$		40	
$T_C = 100^\circ C$		105	
Pulsed collector current, $t_p$ limited by $T_{j,max}$	$I_{C,puls}$	105	
Turn off safe operating area	-	105	
$V_{CE} \leq 1200V, T_j \leq 150^\circ C$			
Gate-emitter voltage	$V_{GE}$	±20	V
Short circuit withstand time <sup>2)</sup>	$t_{SC}$	10	μs
$V_{GE} = 15V, V_{CC} \leq 1200V, T_j \leq 150^\circ C$			
Power dissipation	$P_{tot}$	270	W
$T_C = 25^\circ C$			
Operating junction temperature	$T_j$	-40...+150	°C
Storage temperature	$T_{stg}$	-55...+150	
Soldering temperature, 1.6mm (0.063 in.) from case for 10s	-	260	

<sup>1</sup> J-STD-020 and JESD-022

<sup>2)</sup> Allowed number of short circuits: <1000; time between short circuits: >1s.



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**IGW40T120**
**Thermal Resistance**

Parameter	Symbol	Conditions	Max. Value	Unit
<b>Characteristic</b>				
IGBT thermal resistance, junction – case	$R_{thJC}$		0.45	K/W
Thermal resistance, junction – ambient	$R_{thJA}$		40	

**Electrical Characteristic, at  $T_j = 25^\circ\text{C}$ , unless otherwise specified**

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	
<b>Static Characteristic</b>						
Collector-emitter breakdown voltage	$V_{(BR)CES}$	$V_{GE}=0V, I_C=1.5mA$	1200	-	-	V
Collector-emitter saturation voltage	$V_{CE(sat)}$	$V_{GE} = 15V, I_C=40A$	-	1.7	2.3	
		$T_j=25^\circ\text{C}$	-	2.1	-	
		$T_j=150^\circ\text{C}$	-	2.3	-	
Gate-emitter threshold voltage	$V_{GE(th)}$	$I_C=1.5mA, V_{CE}=V_{GE}$	5.0	5.8	6.5	
Zero gate voltage collector current	$I_{CES}$	$V_{CE}=1200V,$ $V_{GE}=0V$				mA
		$T_j=25^\circ\text{C}$	-	-	0.4	
		$T_j=150^\circ\text{C}$	-	-	4.0	
Gate-emitter leakage current	$I_{GES}$	$V_{CE}=0V, V_{GE}=20V$	-	-	600	nA
Transconductance	$g_{fs}$	$V_{CE}=20V, I_C=40A$	-	21	-	S
Integrated gate resistor	$R_{Gint}$			6		$\Omega$



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**Dynamic Characteristic**

Input capacitance	$C_{iss}$	$V_{CE}=25V,$	-	2500	-	pF
Output capacitance	$C_{oss}$	$V_{GE}=0V,$	-	130	-	
Reverse transfer capacitance	$C_{rss}$	$f=1MHz$	-	110	-	
Gate charge	$Q_{Gate}$	$V_{CC}=960V, I_C=40A$ $V_{GE}=15V$	-	203	-	nC
Internal emitter inductance measured 5mm (0.197 in.) from case	$L_E$		-	13	-	nH
Short circuit collector current <sup>1)</sup>	$I_{C(SC)}$	$V_{GE}=15V, t_{SC} \leq 10\mu s$ $V_{CC} = 600V,$ $T_j = 25^\circ C$	-	210	-	A

**Switching Characteristic, Inductive Load, at  $T_j=25^\circ C$**

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	
<b>IGBT Characteristic</b>						
Turn-on delay time	$t_{d(on)}$	$T_j=25^\circ C,$ $V_{CC}=600V, I_C=40A,$ $V_{GE}=0/15V,$ $R_G=15\Omega,$ $L_\sigma^{(2)}=180nH,$ $C_\sigma^{(2)}=39pF$ Energy losses include "tail" and diode reverse recovery.	-	48	-	ns
Rise time	$t_r$		-	34	-	
Turn-off delay time	$t_{d(off)}$		-	480	-	
Fall time	$t_f$		-	70	-	
Turn-on energy	$E_{on}$		-	3.3	-	mJ
Turn-off energy	$E_{off}$		-	3.2	-	
Total switching energy	$E_{ts}$		-	6.5	-	

**Switching Characteristic, Inductive Load, at  $T_j=150^\circ C$**

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	
<b>IGBT Characteristic</b>						
Turn-on delay time	$t_{d(on)}$	$T_j=150^\circ C$ $V_{CC}=600V, I_C=40A,$ $V_{GE}=0/15V,$ $R_G=15\Omega,$ $L_\sigma^{(2)}=180nH,$ $C_\sigma^{(2)}=39pF$ Energy losses include "tail" and diode reverse recovery.	-	52	-	ns
Rise time	$t_r$		-	40	-	
Turn-off delay time	$t_{d(off)}$		-	580	-	
Fall time	$t_f$		-	120	-	
Turn-on energy	$E_{on}$		-	5.0	-	mJ
Turn-off energy	$E_{off}$		-	5.4	-	
Total switching energy	$E_{ts}$		-	10.4	-	

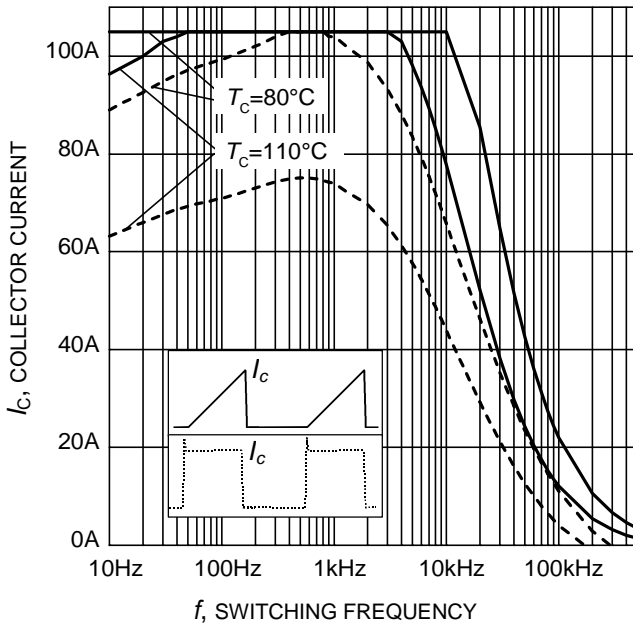
<sup>1)</sup> Allowed number of short circuits: <1000; time between short circuits: >1s.

<sup>2)</sup> Leakage inductance  $L_\sigma$  and Stray capacity  $C_\sigma$  due to dynamic test circuit in Figure E.

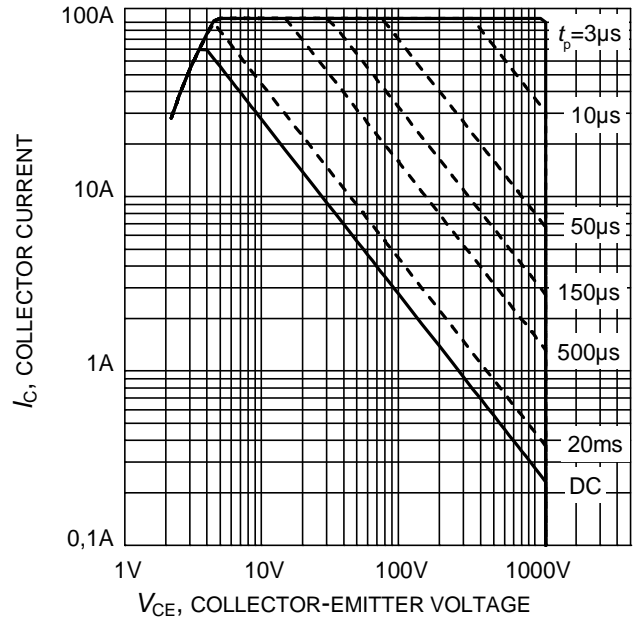


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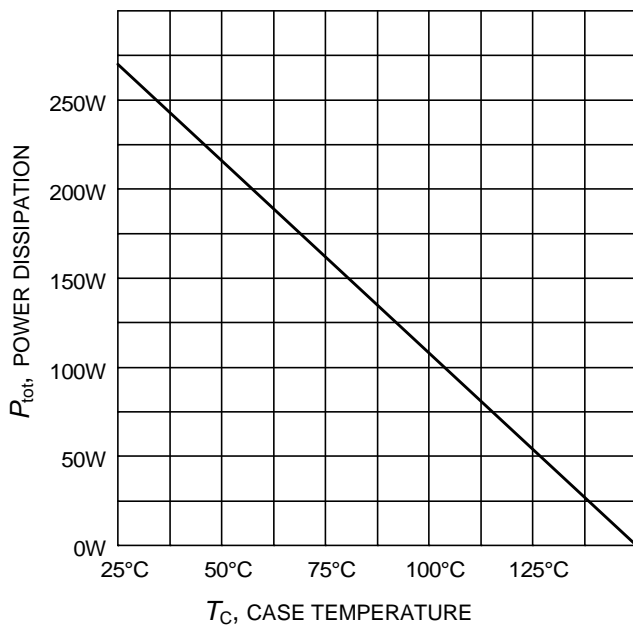
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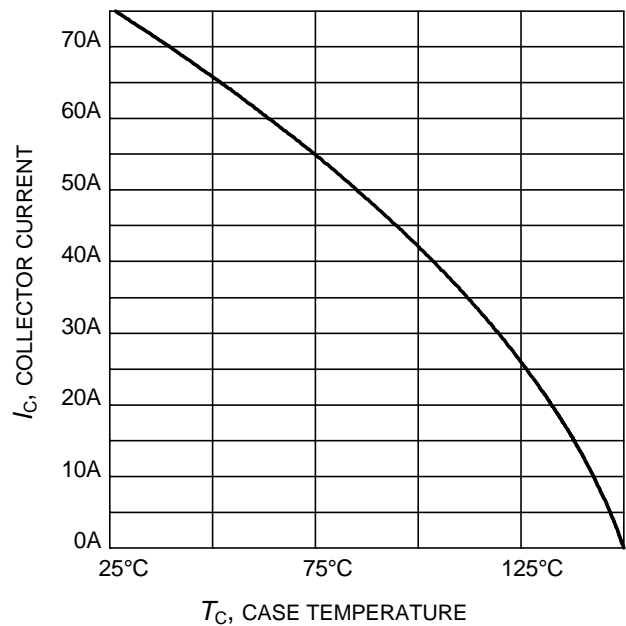
**Figure 1. Collector current as a function of switching frequency**  
 ( $T_j \leq 150^\circ\text{C}$ ,  $D = 0.5$ ,  $V_{CE} = 600\text{V}$ ,  
 $V_{GE} = 0/+15\text{V}$ ,  $R_G = 15\Omega$ )



**Figure 2. Safe operating area**  
 ( $D = 0$ ,  $T_C = 25^\circ\text{C}$ ,  
 $T_j \leq 150^\circ\text{C}$ ;  $V_{GE} = 15\text{V}$ )



**Figure 3. Power dissipation as a function of case temperature**  
 ( $T_j \leq 150^\circ\text{C}$ )

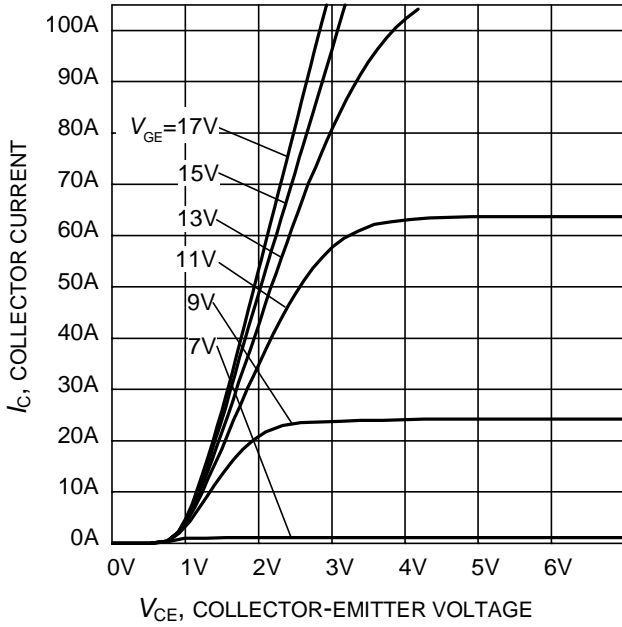


**Figure 4. Collector current as a function of case temperature**  
 ( $V_{GE} \geq 15\text{V}$ ,  $T_j \leq 150^\circ\text{C}$ )

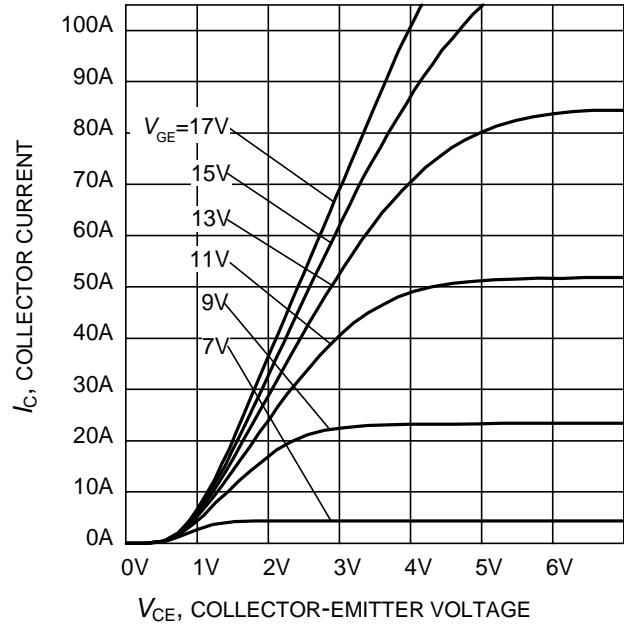


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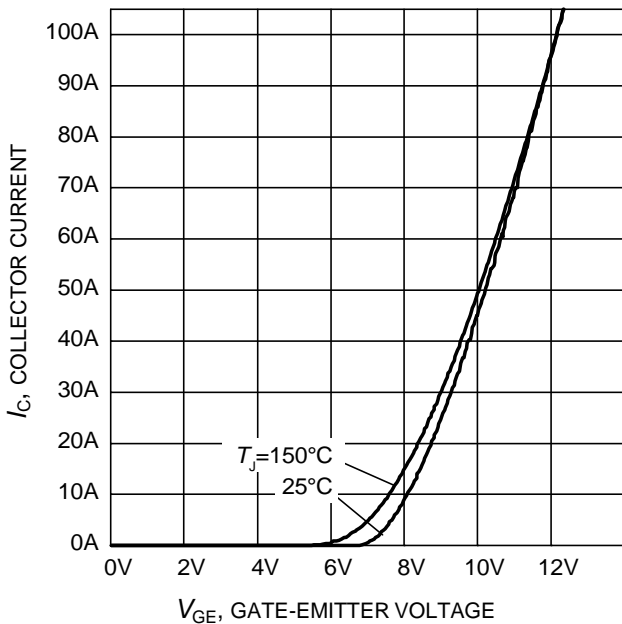
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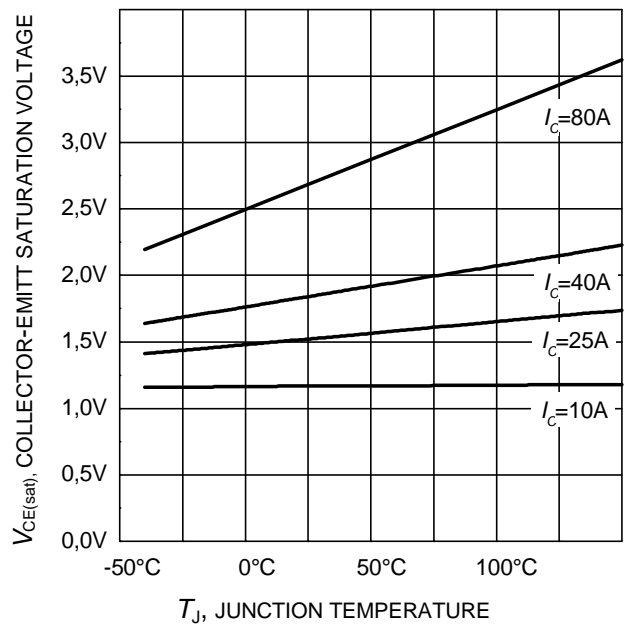
**Figure 5. Typical output characteristic**  
( $T_j = 25^\circ\text{C}$ )



**Figure 6. Typical output characteristic**  
( $T_j = 150^\circ\text{C}$ )



**Figure 7. Typical transfer characteristic**  
( $V_{CE} = 20\text{V}$ )

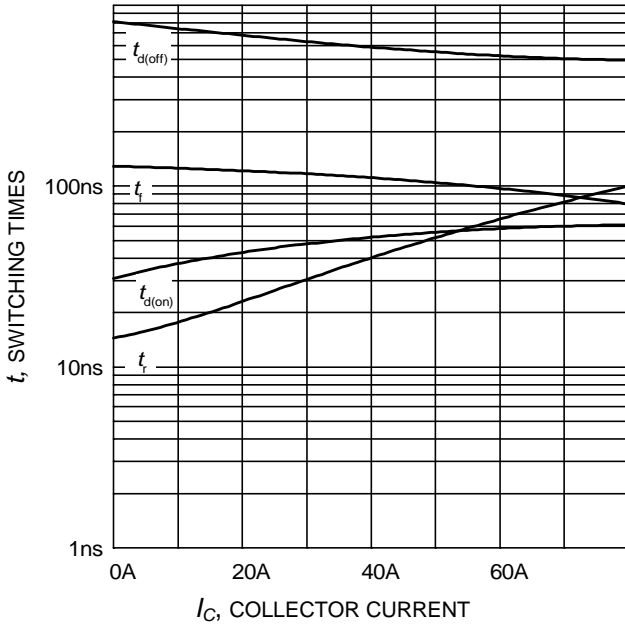


**Figure 8. Typical collector-emitter saturation voltage as a function of junction temperature**  
( $V_{GE} = 15\text{V}$ )

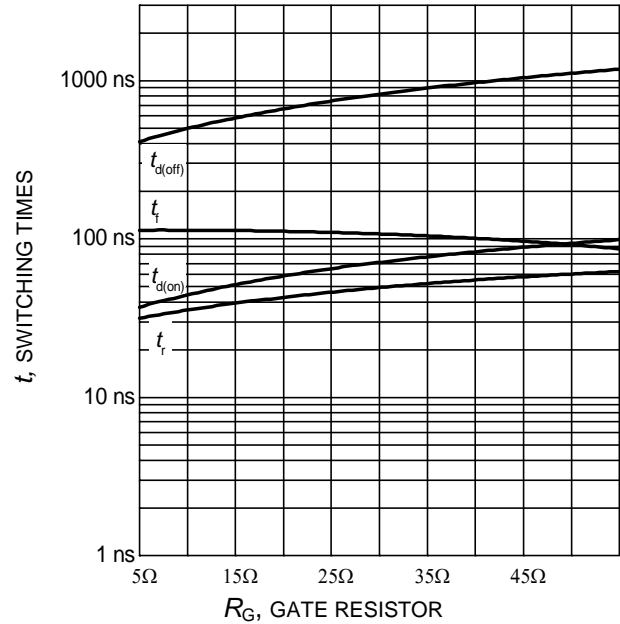


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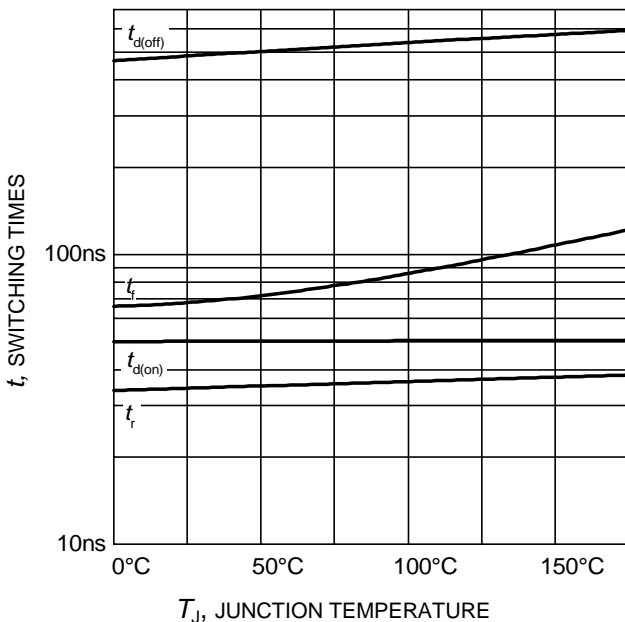
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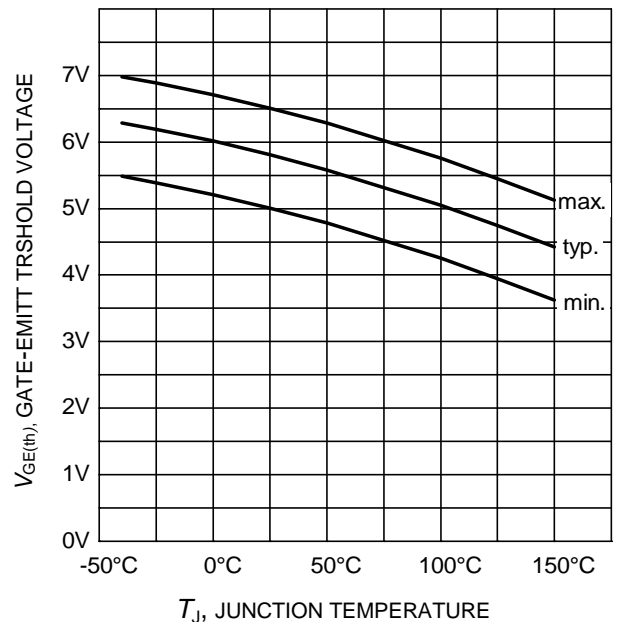
**Figure 9. Typical switching times as a function of collector current**  
 (inductive load,  $T_J=150^{\circ}\text{C}$ ,  $V_{CE}=600\text{V}$ ,  $V_{GE}=0/15\text{V}$ ,  $R_G=15\Omega$ , Dynamic test circuit in Figure E)



**Figure 10. Typical switching times as a function of gate resistor**  
 (inductive load,  $T_J=150^{\circ}\text{C}$ ,  $V_{CE}=600\text{V}$ ,  $V_{GE}=0/15\text{V}$ ,  $I_C=40\text{A}$ , Dynamic test circuit in Figure E)



**Figure 11. Typical switching times as a function of junction temperature**  
 (inductive load,  $V_{CE}=600\text{V}$ ,  $V_{GE}=0/15\text{V}$ ,  $I_C=40\text{A}$ ,  $R_G=15\Omega$ , Dynamic test circuit in Figure E)

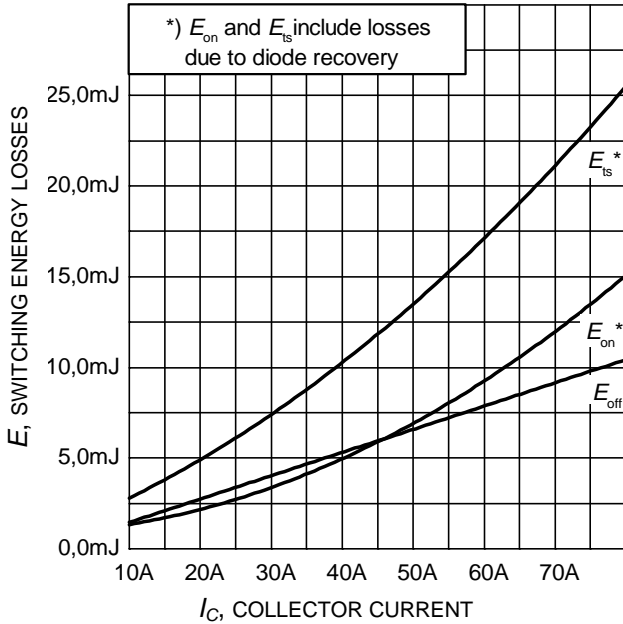


**Figure 12. Gate-emitter threshold voltage as a function of junction temperature**  
 ( $I_C = 1.5\text{mA}$ )

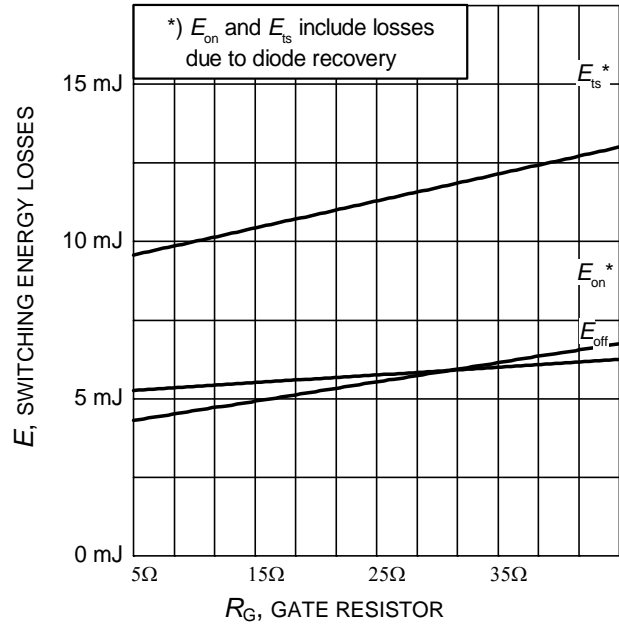


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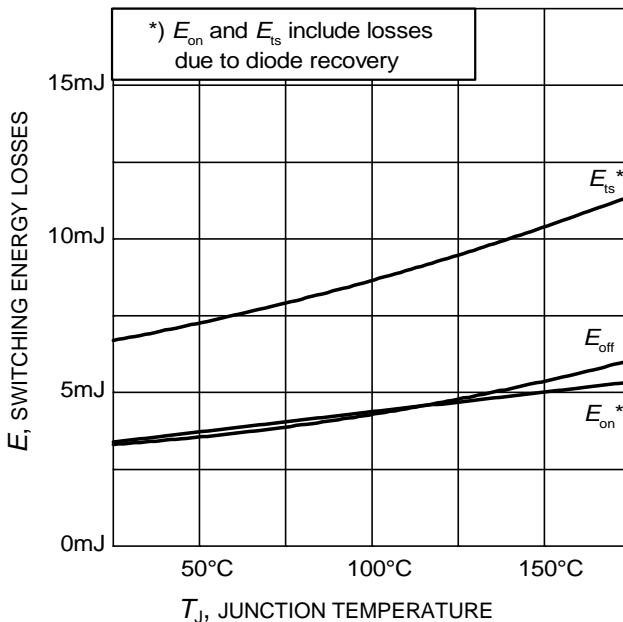
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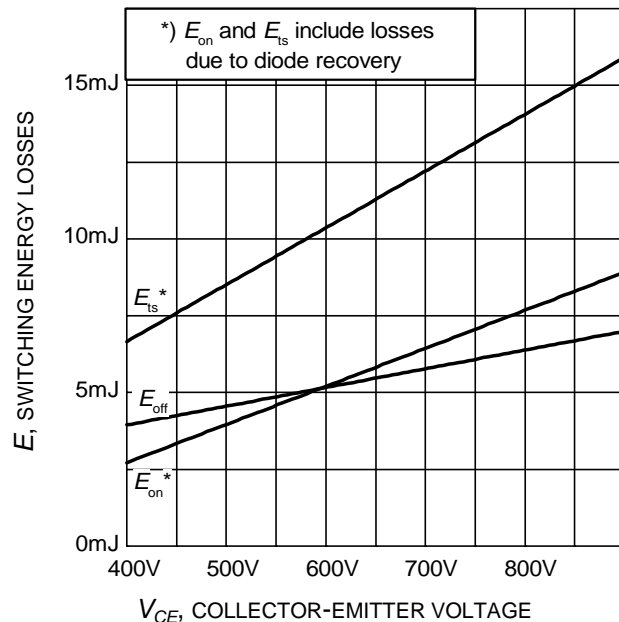
**Figure 13. Typical switching energy losses as a function of collector current**  
 (inductive load,  $T_J=150^\circ\text{C}$ ,  $V_{CE}=600\text{V}$ ,  $V_{GE}=0/15\text{V}$ ,  $R_G=15\Omega$ , Dynamic test circuit in Figure E)



**Figure 14. Typical switching energy losses as a function of gate resistor**  
 (inductive load,  $T_J=150^\circ\text{C}$ ,  $V_{CE}=600\text{V}$ ,  $V_{GE}=0/15\text{V}$ ,  $I_C=40\text{A}$ , Dynamic test circuit in Figure E)



**Figure 15. Typical switching energy losses as a function of junction temperature**  
 (inductive load,  $V_{CE}=600\text{V}$ ,  $V_{GE}=0/15\text{V}$ ,  $I_C=40\text{A}$ ,  $R_G=15\Omega$ , Dynamic test circuit in Figure E)



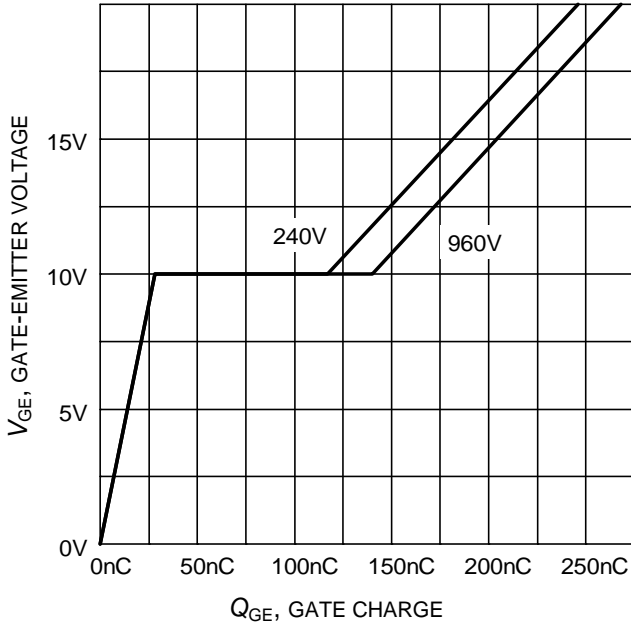
**Figure 16. Typical switching energy losses as a function of collector emitter voltage**  
 (inductive load,  $T_J=150^\circ\text{C}$ ,  $V_{GE}=0/15\text{V}$ ,  $I_C=40\text{A}$ ,  $R_G=15\Omega$ , Dynamic test circuit in Figure E)



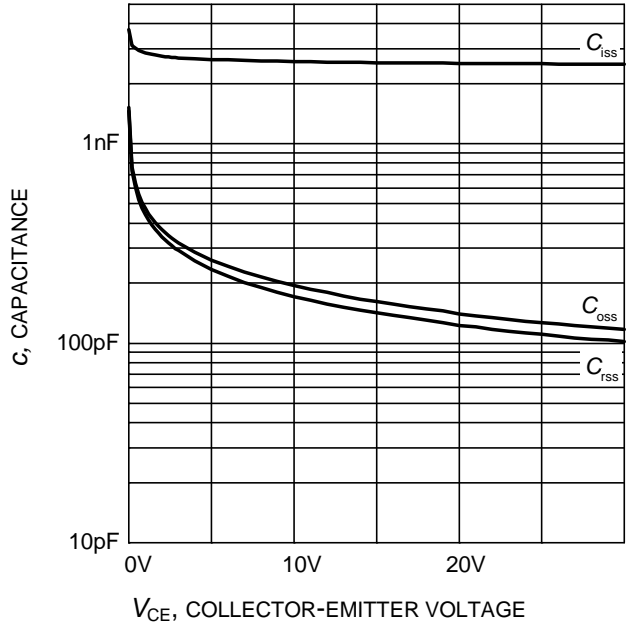


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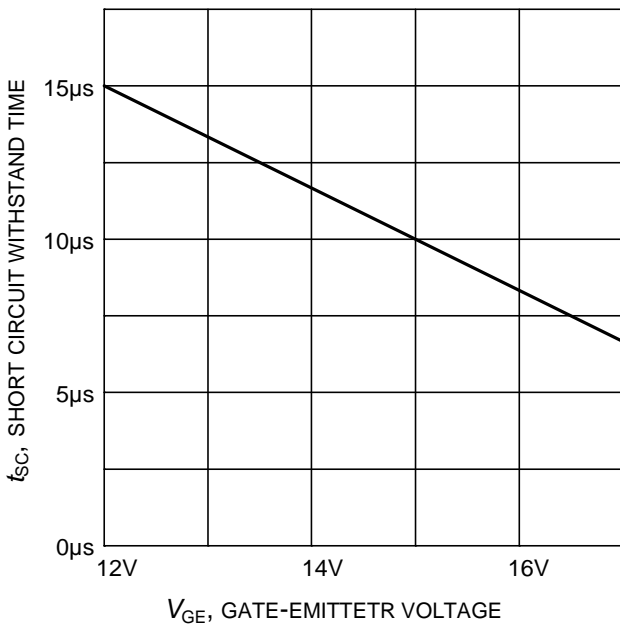
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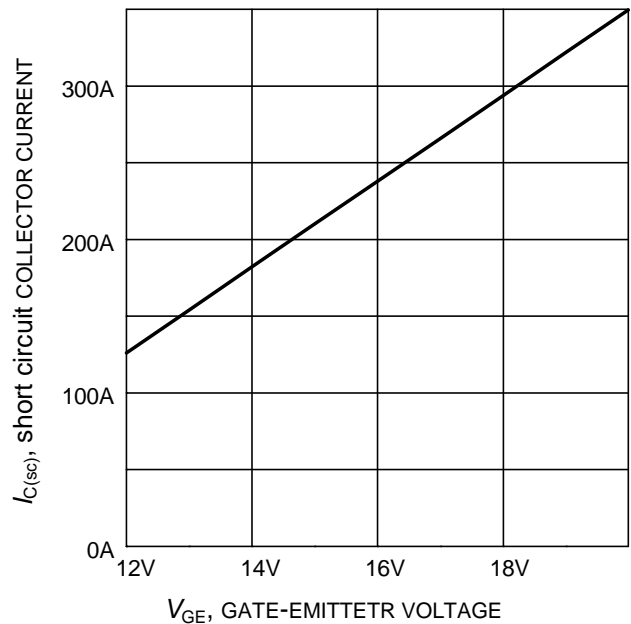
**Figure 17. Typical gate charge**  
( $I_C=40$  A)



**Figure 18. Typical capacitance as a function of collector-emitter voltage**  
( $V_{GE}=0V$ ,  $f = 1$  MHz)



**Figure 19. Short circuit withstand time as a function of gate-emitter voltage**  
( $V_{CE}=600V$ , start at  $T_J=25^\circ C$ )

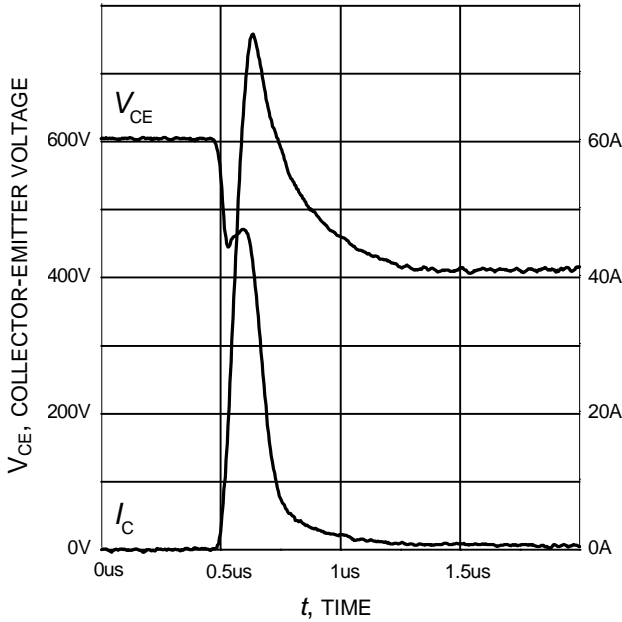


**Figure 20. Typical short circuit collector current as a function of gate-emitter voltage**  
( $V_{CE} \leq 600V$ ,  $T_J \leq 150^\circ C$ )

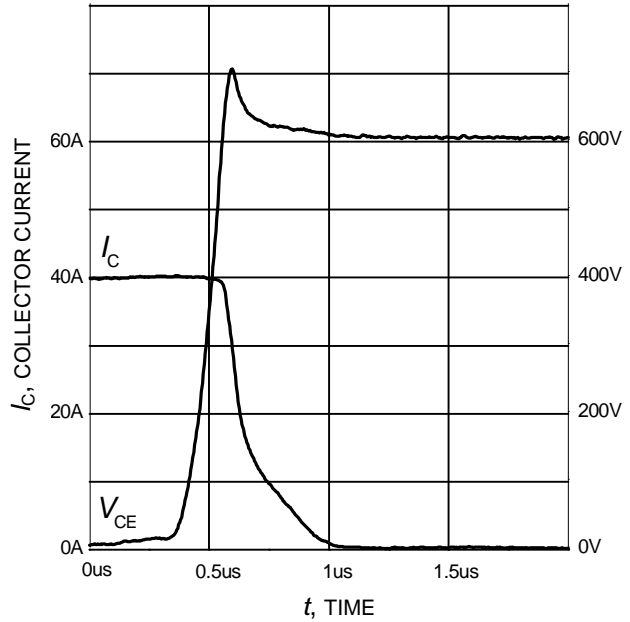


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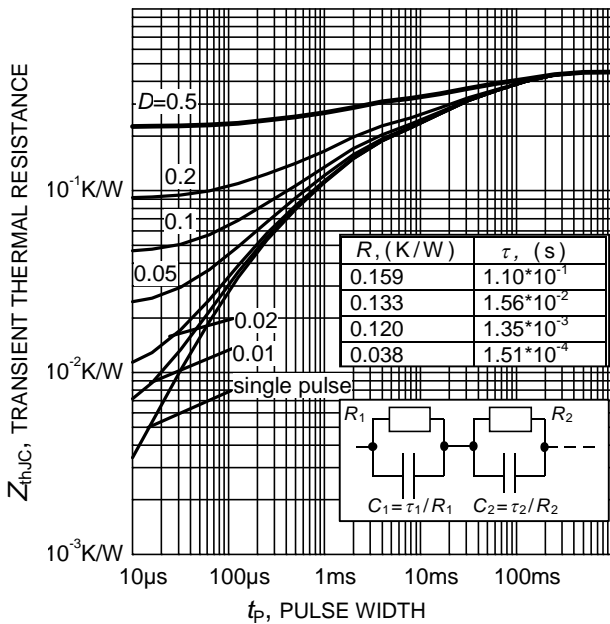
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**Figure 21. Typical turn on behavior**  
 ( $V_{GE}=0/15V$ ,  $R_G=15\Omega$ ,  $T_j = 150^\circ C$ ,  
 Dynamic test circuit in Figure E)



**Figure 22. Typical turn off behavior**  
 ( $V_{GE}=15/0V$ ,  $R_G=15\Omega$ ,  $T_j = 150^\circ C$ ,  
 Dynamic test circuit in Figure E)



**Figure 23. IGBT transient thermal resistance**  
 ( $D = t_p / T$ )

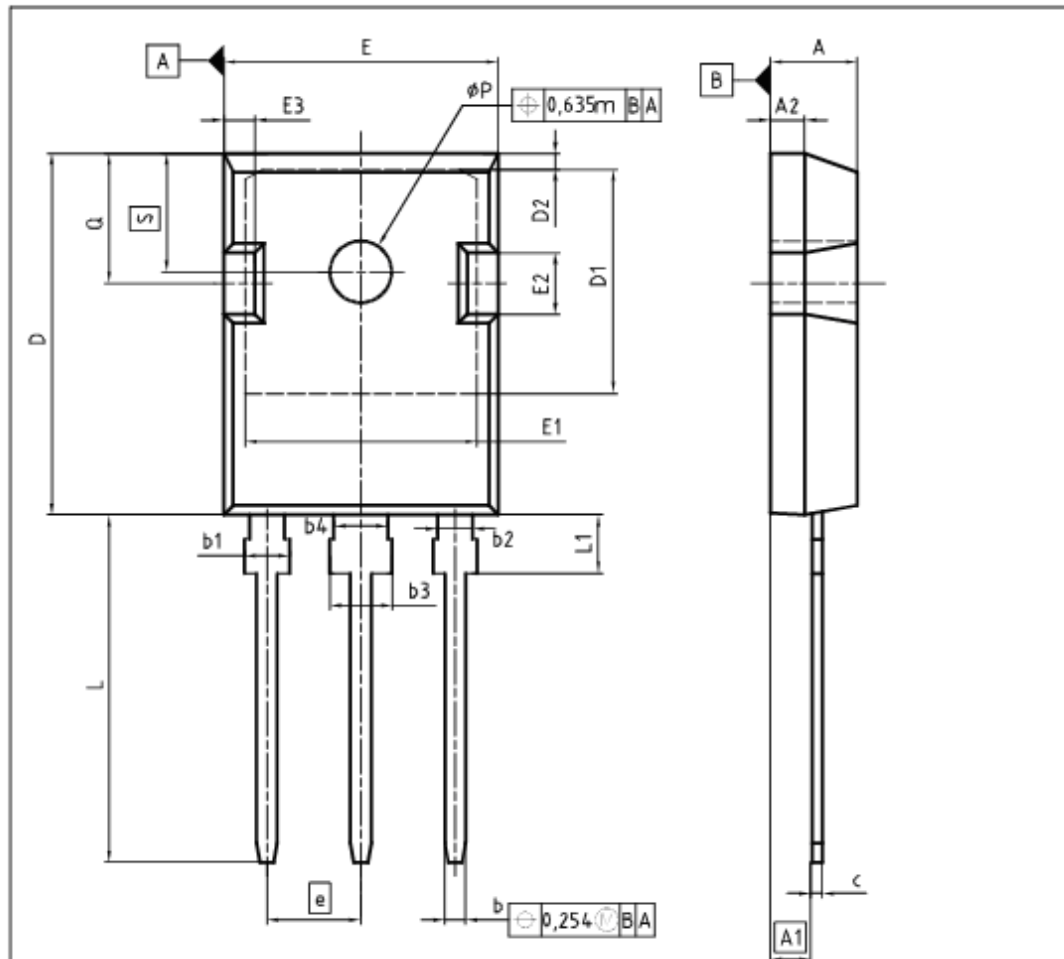


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PG-TO247-3

TO247-3



DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	4.83	5.21	0.190	0.205
A1	2.27	2.54	0.089	0.100
A2	1.85	2.16	0.073	0.085
b	1.07	1.33	0.042	0.052
b1	1.90	2.41	0.075	0.095
b2	1.90	2.16	0.075	0.085
b3	2.87	3.38	0.113	0.133
b4	2.87	3.13	0.113	0.123
c	0.55	0.68	0.022	0.027
D	20.80	21.10	0.819	0.831
D1	16.25	17.65	0.640	0.695
D2	0.95	1.35	0.037	0.053
E	15.70	16.13	0.618	0.635
E1	13.10	14.15	0.516	0.557
E2	3.68	5.10	0.145	0.201
E3	1.00	2.60	0.039	0.102
e	5.44		0.214	
N	3		3	
L	19.80	20.32	0.780	0.800
L1	4.10	4.47	0.161	0.176
phi P	3.50	3.70	0.138	0.146
Q	5.49	6.00	0.216	0.236
S	6.04	6.30	0.238	0.248

DOCUMENT NO.  
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SCALE  

 7.5mm

EUROPEAN PROJECTION

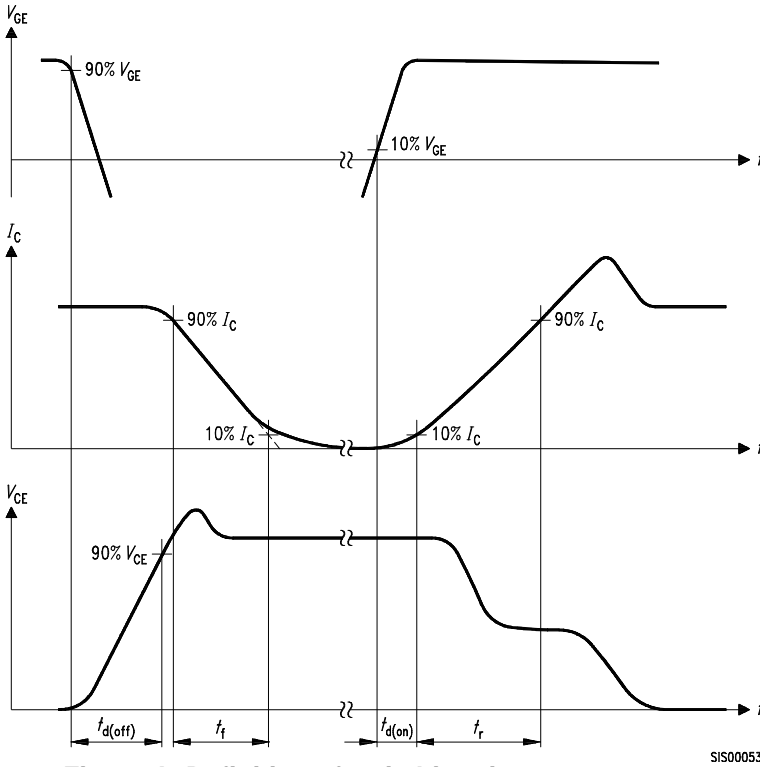
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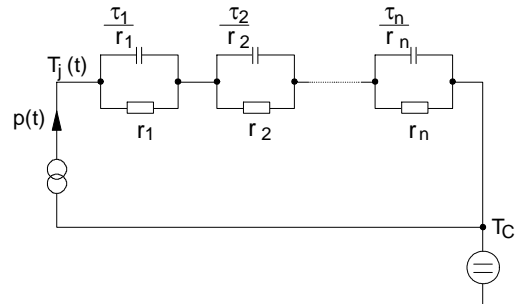


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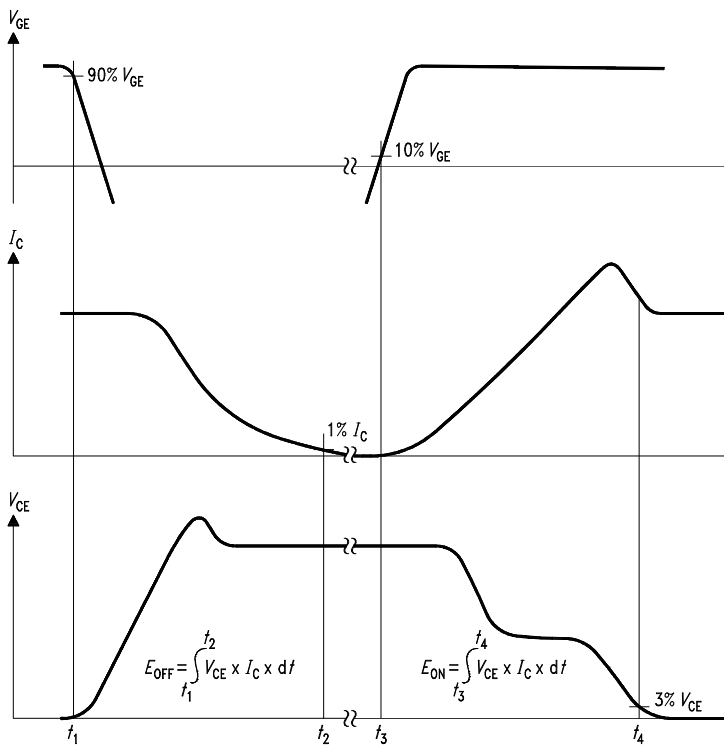
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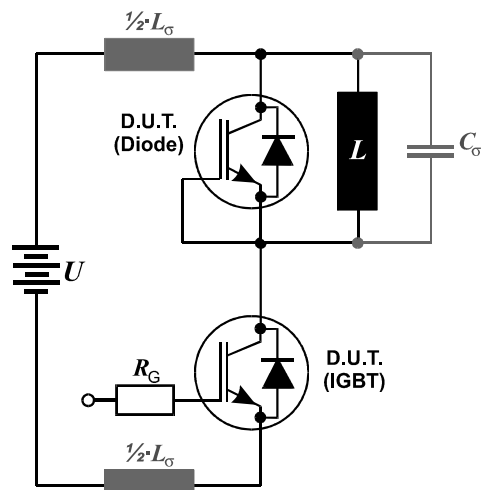
**Figure A. Definition of switching times**



**Figure D. Thermal equivalent circuit**



**Figure B. Definition of switching losses**



**Figure E. Dynamic test circuit**  
 Leakage inductance  $L_{\sigma} = 180\text{nH}$   
 and Stray capacity  $C_{\sigma} = 39\text{pF}$ .



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TrenchStop® Series

IGW40T120

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